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## RECEIVED

## IN THE UNITED STATES PATENT & TRADEMARK OF TOP 6 2002

IN RE APPLICATION OF:

TECHNOLOGY CENTER 2800

TATSUYA OHGURO

: EXAMINER: DANA FARAHANI

SERIAL NO.: 09/409,393

H57 mult At

FILED: FEBRUARY 28, 2002

: GROUP ART UNIT: 2814

FOR: SEMICONDUCTOR DEVICE

APPLIED TO A VARIABLE

CAPACITANCE CAPACITOR

AND AMPLIFIER

## **AMENDMENT**

ASSISTANT COMMISSIONER FOR PATENTS WASHINGTON, D.C. 20231

SIR:

In response to the Official Office Action dated June 24, 2002, please amend the above-identified patent application as follows:

## IN THE CLAIMS

Please amend Claim 7 as shown in clean form below. A marked-up copy of the amended claim is attached.

- 7. (Amended) A semiconductor device comprising:
- a semiconductor substrate;
- a first conductivity type well area formed in a surface area of the semiconductor

substrate:

a plurality of element isolation areas formed in the well area;

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(3°%)